

### 12V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
	$11m\Omega$ @ $V_{GS} = -4.5V$	-11A
-12V	$14m\Omega @ V_{GS} = -3.7V$	-9.7A
	19mΩ @ V <sub>GS</sub> = -2.5V	-8.3A
	$30m\Omega$ @ $V_{GS} = -1.8V$	-6.6A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

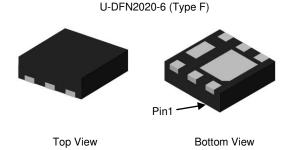
- Battery Management Application
- Power Management Functions
- DC-DC Converters

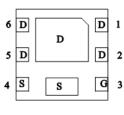
#### **Features**

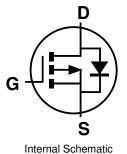
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- · Fast Switching Speed
- 100% Unclamped Inductive Switching (Test in Production) Ensures More Reliability
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.007 grams (Approximate)







Pin Out Bottom View

# Ordering Information (Note 5)

Part Number	Case	Packaging
DMP1009UFDFQ-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP1009UFDFQ-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



FZ = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2017		2018	2019		2020	2021		2022	2023		2024
Code	Е		F	G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	-12	V		
Gate-Source Voltage	$V_{GSS}$	±8	V		
	Steady	$T_A = +25^{\circ}C$	- I <sub>D</sub>	-11	۸
Continuous Dunin Commant V 4 5V (Note 7)	State	T <sub>A</sub> = +70°C		-8.7	A
Continuous Drain Current V <sub>GS</sub> = -4.5V (Note 7)	t<5s	T <sub>A</sub> = +25°C	· I <sub>D</sub>	-15	^
		T <sub>A</sub> = +70°C		-12	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-70	Α		
Maximum Body Diode Continuous Current (Note 7)	aximum Body Diode Continuous Current (Note 7)			-2.5	Α
Avalanche Current (Note 8) L = 0.1mH	I <sub>AS</sub>	-24	Α		
Avalanche Energy (Note 8) L = 0.1mH	E <sub>AS</sub>	31	mJ		

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.8	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Ъ	152	°C/W	
Thermal nesistance, buildion to Ambient (Note 6)	t<5s R <sub>0JA</sub>		81	C/VV	
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.0	W	
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	Ъ	63		
Thermal Resistance, Junction to Ambient (Note 7)	t<5s	$R_{\theta JA}$	34	°C/W	
Thermal Resistance, Junction to Case (Note 7)	Steady State	$R_{ heta JC}$	15		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-12	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-100	nA	$V_{DS} = -9.6V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	1	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.3	_	-1.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
			8.3	11		$V_{GS} = -4.5V, I_D = -5A$
Static Drain-Source On-Resistance	D		9	14	mΩ	$V_{GS} = -3.7V, I_D = -5A$
Static Diani-Source Off-Nesistance	R <sub>DS(ON)</sub>	_	12	19	1112.2	$V_{GS} = -2.5V$ , $I_{D} = -4A$
			16	30		$V_{GS} = -1.8V, I_D = -1A$
Diode Forward Voltage	$V_{SD}$	_	-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -10A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C <sub>iss</sub>	_	1860	_		
Output Capacitance	Coss	_	498	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	416	_		1 - 1.000112
Gate Resistance	$R_{g}$	_	11	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_g$	_	26	_		
Total Gate Charge (V <sub>GS</sub> = -8V)	Qg	_	44	_	nC	V <sub>DS</sub> = -6V. I <sub>D</sub> = -10A
Gate-Source Charge	Q <sub>gs</sub>	_	3.3	_	IIC	$V_{DS} = -6V$ , $I_D = -10A$
Gate-Drain Charge	$Q_{gd}$	_	8.1	_		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7.0	_		
Turn-On Rise Time	t <sub>R</sub>	_	10.6	_		$V_{DS} = -6V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	62.2	_	ns	$R_g = 1\Omega$ , $I_D = -8A$
Turn-Off Fall Time	t <sub>F</sub>	_	61	_		
Reverse Recovery Time	t <sub>RR</sub>	_	34.4	_	ns	1 100 4:/44 5000/
Reverse Recovery Charge	$Q_{RR}$	_	28.1	_	nC	I <sub>F</sub> = -12A, di/dt = 500A/μs

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

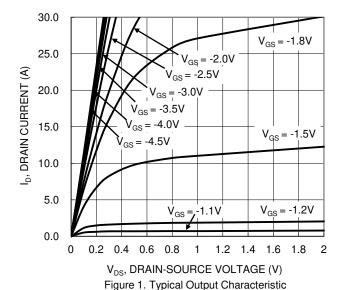
<sup>8.</sup>  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

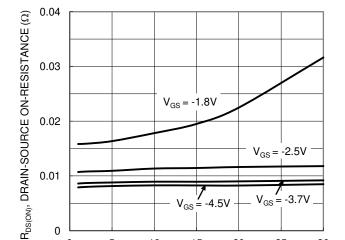
<sup>9.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>10.</sup> Guaranteed by design. Not subject to product testing.









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I<sub>D</sub>, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

15

20

25

30

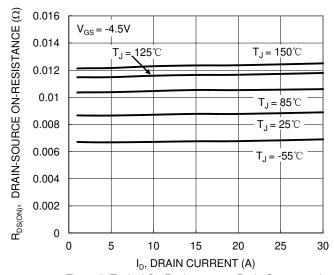


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

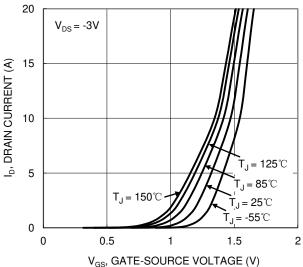


Figure 2. Typical Transfer Characteristic

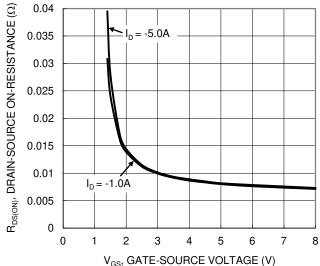


Figure 4. Typical Transfer Characteristic

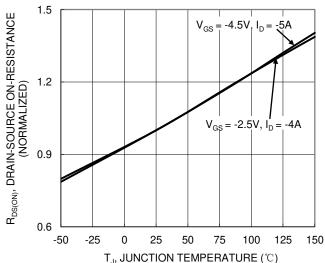


Figure 6. On-Resistance Variation with Temperature





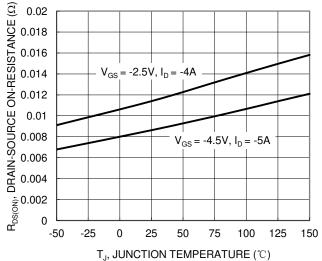
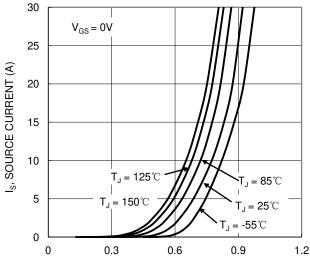
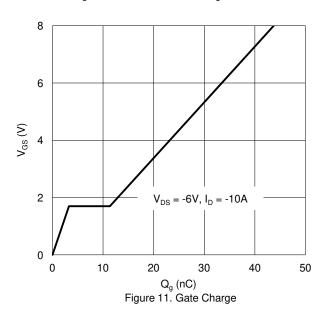


Figure 7. On-Resistance Variation with Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



 $V_{\text{GS(TH)}},$  GATE THRESHOLD VOLTAGE (V) 0.8  $I_D = -1 \text{mA}$ 0.6  $I_{D} = -250 \mu A$ 0.4 0.2 0 -50 -25 0 25 50 75 100 125 150

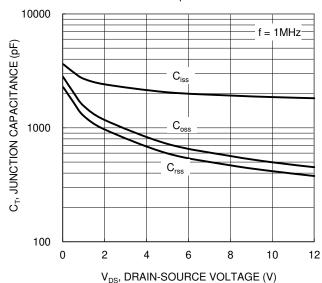
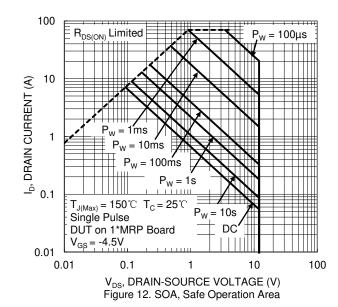


Figure 10. Typical Junction Capacitance





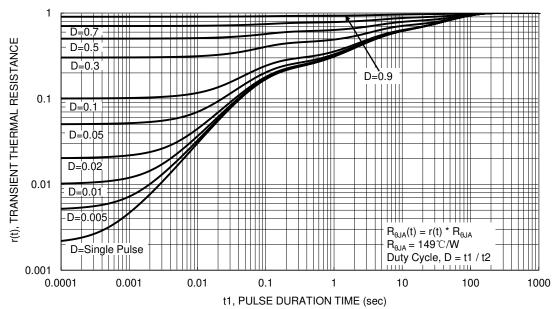


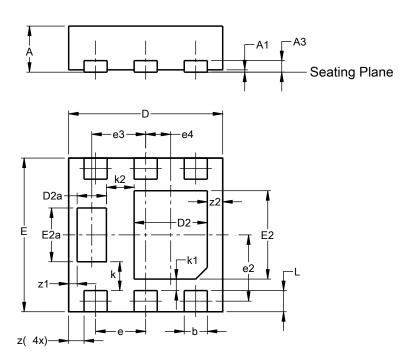
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## U-DFN2020-6 (Type F)

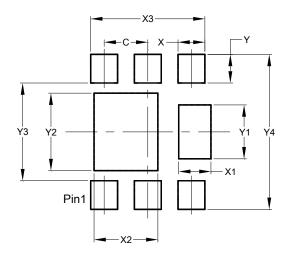


U-DFN2020-6									
(Type F)									
Dim	Min	· /r							
Α	0.57	0.63	0.60						
A1	0.00								
A3	1	-	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
Е	1.95	2.05	2.00						
E2	1.05	1.25	1.15						
E2a	0.65 0.75 0.70								
е		0.65 BSC							
e2	0.863 BSC								
е3		0.70 BS	_						
e4	0.325 BSC								
k	0.37 BSC								
k1	0.15 BSC								
k2	0.36 BSC								
L	0.225 0.325 0.275								
Z	0.20 BSC								
<b>z</b> 1	0.110 BSC								
z2	0.20 BSC								
All C	All Dimensions in mm								

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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